

AMENDMENT TO SPECIFICATION

Please replace paragraph [0029] of the specification with the following amended paragraph [0029]:

[0029] Figure 4 shows a semiconductor device before forming a stressed transistor channel having a silicon substrate 12 with a doped salicide region 24. On top of the silicon substrate 12 is a gate oxide 14, and on top of the gate oxide 14 is a polysilicon gate 16. Gate sidewalls 18 are formed on the sides of the polysilicon gate 16. A gate salicide region 26 is formed on the polysilicon gate 16 to complete the gate stack 19. Together, the polysilicon gate 16 and gate sidewalls 18 form the gate stack 19. For purposes of this description, the gate stack 19 may also include, for example, the polysilicon gate 16, gate sidewalls 18, and gate salicide region 26. The structure thus described is formed in any conventional manner known to those of skill in the art.